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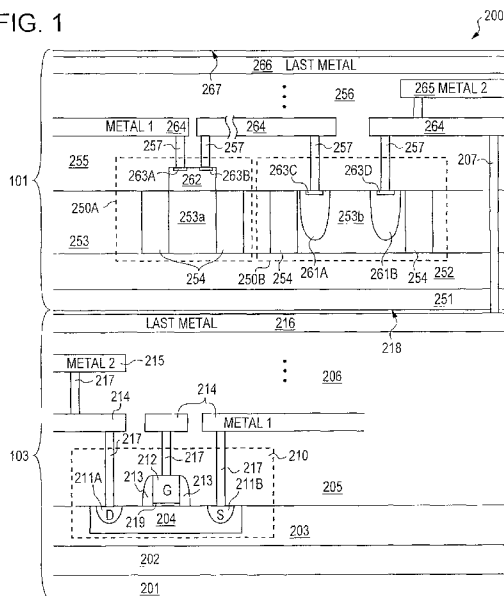
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(54) Title: METHOD OF FORMING PHOTONICS STRUCTURES

FIG. 1



(57) Abstract: The disclosed embodiments relate to an integrated circuit structure and methods of forming them in which photonic devices are formed on the back end of fabricating a CMOS semiconductor structure containing electronic devices. Doped regions associated with the photonic devices are formed using microwave annealing for dopant activation.